



Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced rugged : Tin plated leads, solderable per 002 and JESD22-B102

- **Polarity:** As marked

■Maximum Ratings (T_a=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Device marking code			MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Repetitive Peak Reverse Voltage	VRRM	V	80	100	120	150	200
Average Rectified Output Current @60Hz sine wave, R-load, T _a =25	I _O	A	10				
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, T _a =25	I _{FSM}	A	100				
Current Squared Time @1ms≤t≤8.3ms T _j =25	I ² t	A ² s	41				

Storage Temperature T_{stg}

				MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Maximum instantaneous forward voltage drop per diode	V _{FM}	V	I _{FM} =5.0A	0.85		0.9		0.95
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} T _a =25	0.1				
	I _{RRM2}		V _{RM} =V _{RRM} T _a =100	20				

Note1:Pulse test:300uS pulse width,1% duty cycle

Note2:Pulse test:pulse width 40mS



MBR1080CT THRU MBR10200CT

■ Thermal Characteristics ($T_a=25$ Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR1080CT	MBR10100CT	MBR10120CT	MBR10150CT	MBR10200CT
Thermal Resistance	Between junction and case	$R_{\theta j-c}$	$^{\circ}W$					
				2.0				

■ Ordering Information (Example)

PREFERRED P/N	
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MBR1080CT THRU MBR10200CT

■Outline Dio λ

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